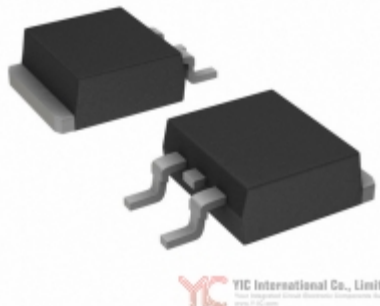










	<h2 style="color: red;">FQB32N12V2TM</h2>	
	Hersteller-Teilenummer:	FQB32N12V2TM
	Hersteller / Marke:	AMI Semiconductor / ON Semiconductor
	Teil der Beschreibung:	MOSFET N-CH 120V 32A D2PAK
	Datenblätter:	 FQB32N12V2TM.pdf
	RoHs Status:	Bleifrei / RoHS-konform
	Lagerzustand:	New original, 33216 pcs Stock Available.
	Liefern von:	Hong Kong
	Versandweg:	DHL/Fedex/TNT/UPS/EMS
<p>Image may be representation. See specs for product details.</p>		

Spezifikationen

Teilenummer	FQB32N12V2TM
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 120V 32A D2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	33216 pcs Stock
detaillierte Beschreibung	N-Channel 120V 32A (Tc) 3.75W (Ta), 150W (Tc)
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 175°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D ² PAK (TO-263AB)
Verlustleistung (max)	3.75W (Ta), 150W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	120V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	32A (Tc)
Rds On (Max) @ Id, Vgs	50 mOhm @ 16A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	53nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1860pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±30V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)

FQB32N12V2TM ist neu im Original, Suche FQB32N12V2TM Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB32N12V2TM AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB32N12V2TM: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>FQB32N30 FAIRCHILD FQB32N30 FAIRCHILD</p>	 <p>FQB32N12V2TM Fairchild/ON Semiconductor MOSFET N-CH 120V 32A D2PAK</p>	 <p>FQB32N20CTM Fairchild/ON Semiconductor MOSFET N-CH 200V 28A D2PAK</p>	 <p>FQB30N06TM_NL FAIRCHI</p>
 <p>FQB32N12V2 FSC FQB32N12V2 FSC</p>	 <p>FQB32N20 FSC FQB32N20 FSC</p>	 <p>FQB32N20CTM AMI Semiconductor / ON Semiconductor MOSFET N-CH 200V 28A D2PAK</p>	 <p>FQB32N20C F FQB32N20C F</p>

heiße Teile

Mehr

⊕ FQB24N08TM	↔ FQB25N33	⇒ FQB25N33TM	D FQB25N33TM	⇒ FQB25N33TM_F085
⊕ FQB27N25TM	⊕ FQB27P06	D FQB27P06TM	⇒ FQB27P06TM	⇒ FQB2N50C
⊕ FQB2N60TM	⊕ FQB2N60TM	⊕ FQB2N80TM	↔ FQB2N80TM	⇒ FQB2NA90TM
D FQB2NA90TM	⊕ FQB2P25TM	⊕ FQB2P25TM	⊕ FQB30N06	⇒ FQB30N06L
⇒ FQB30N06LTM	↔ FQB30N06LTM	⊕ FQB30N06TM	⊕ FQB30N06TM	⇒ FQB32N12V2
↔ FQB32N12V2TM	⇒ FQB32N20	D FQB32N20C	⊕ FQB32N20CTM	⊕ FQB32N20CTM
⊕ FQB32N30	D FQB33N10	⇒ FQB33N10L	↔ FQB33N10LTM	⇒ FQB33N10LTM
⊕ FQB33N10TM	⊕ FQB33N10TM	↔ FQB34N20	⇒ FQB34N20L	⇒ FQB34N20LTM
⊕ FQB34N20LTM	⊕ FQB34N20TM	⊕ FQB34N20TM_AM002	D FQB34P10	⇒ FQB34P10TM
↔ FQB34P10TM	⊕ FQB34P10TM_F085	⊕ FQB3N25TM	⊕ FQB3N25TM	⇒ FQB3N30TM

Contact us: Info@Y-IC.com

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